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### AAP Gen 7 (TO-240AA) Power Modules Thyristor/Thyristor, 95 A



ADD-A-PAK

PRIMARY CHARACTERISTICS						
I <sub>T(AV)</sub>	95 A					
Туре	Modules - thyristor, standard					
Package	AAP Gen 7 (TO-240AA)					

#### **MECHANICAL DESCRIPTION**

The AAP Gen 7 (TO-240AA), new generation of AAP module, combines the excellent thermal performances obtained by the usage of exposed direct bonded copper substrate, with advanced compact simple package solution and simplified internal structure with minimized number of interfaces.

#### **FEATURES**

- · High voltage
- Industrial standard package



- · Low thermal resistance
- UL approved file E78996
- · Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>

#### **BENEFITS**

- Excellent thermal performances obtained by the usage of exposed direct bonded copper substrate
- Up to 1600 V
- · High surge capability
- · Easy mounting on heatsink

#### **ELECTRICAL DESCRIPTION**

These modules are intended for general purpose high voltage applications such as high voltage regulated power supplies, lighting circuits, temperature and motor speed control circuits, UPS and battery charger.

MAJOR RATINGS AND CHARACTERISTICS						
SYMBOL	MBOL CHARACTERISTICS VALUES					
I <sub>T(AV)</sub>	85 °C	95				
I <sub>T(RMS)</sub>		150	Α			
I <sub>TSM</sub>	50 Hz	2000	A			
	60 Hz	2094				
I <sup>2</sup> t	50 Hz	20	kA <sup>2</sup> s			
1-1	60 Hz	18.26	KA-5			
l²√t		200	kA²√s			
V <sub>RRM</sub>	Range	400 to 1600	V			
T <sub>Stg</sub>		-40 to +125	°C			
T <sub>J</sub>		-40 to +125	°C			



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#### **ELECTRICAL SPECIFICATIONS**

VOLTAGE RATINGS								
TYPE NUMBER	VOLTAGE CODE	V <sub>RRM</sub> , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	V <sub>DRM</sub> , MAXIMUM REPETITIVE PEAK OFF-STATE VOLTAGE, GATE OPEN CIRCUIT V	I <sub>RRM,</sub> I <sub>DRM</sub> AT 125 °C mA			
	04	400	500	400				
VS-VSK.91	08	800	900	800	15			
12		1200	1300	1200	13			
	16	1600	1700	1600				

ON-STATE CONDUCTION						
PARAMETER	SYMBOL		TEST CONDITIONS			UNITS
Maximum average on-state current	I <sub>T(AV)</sub>	180° conduction T <sub>C</sub> = 85 °C	180° conduction, half sine wave, $T_C = 85$ °C			А
Maximum continuous RMS on-state current		DC			150	
Maximum continuous nivis on-state current	I <sub>T(RMS)</sub>	T <sub>C</sub>			78	°C
		t = 10 ms	No voltage		2000	
Maximum peak, one-cycle non-repetitive		t = 8.3 ms	reapplied	Sinusoidal	2094	^
on-state current	I <sub>TSM</sub>	t = 10 ms	100 % V <sub>RRM</sub>	half wave, initial $T_J = T_J maximum$	1682	Α
		t = 8.3 ms	reapplied		1760	
		t = 10 ms	No voltage		20	kA <sup>2</sup> s
Maximum I <sup>2</sup> t for fusing	121	t = 8.3 ms	reapplied		18.26	
	l <sup>2</sup> t	t = 10 ms	100 % V <sub>RRM</sub>	Initial $T_J = T_J$ maximum	14.14	
		t = 8.3 ms	reapplied		12.91	
Maximum I²√t for fusing	I <sup>2</sup> √t (1)		t = 0.1 ms to 10 ms, no voltage reapplied  T <sub>.I</sub> = T <sub>.I</sub> maximum			kA²√s
	. (2)	Low level (3)	T <sub>J</sub> = T <sub>J</sub> maximum		0.97	V
Maximum value of threshold voltage	V <sub>T(TO)</sub> (2)	High level (4)			1.1	
Maximum value of on-state	(2)	Low level (3)	T <sub>J</sub> = T <sub>J</sub> maximum		2.76	mΩ
slope resistance	r <sub>t</sub> <sup>(2)</sup>	High level (4)			2.38	
Maximum on-state voltage drop	$V_{TM}$	$I_{TM} = \pi \times I_{T(AV)}$	$I_{T(AV)}$ $T_J = 25  ^{\circ}C$		1.73	V
Maximum non-repetitive rate of rise of turned on current	dl/dt	$T_J = 25$ °C, from 0.67 $V_{DRM}$ , $I_{TM} = \pi \times I_{T(AV)}$ , $I_g = 500$ mA, $t_r < 0.5 \mu s$ , $t_p > 6 \mu s$			150	A/μs
Maximum holding current	I <sub>H</sub>	T <sub>J</sub> = 25 °C, anode supply = 6 V, resistive load, gate open circuit			250	mA
Maximum latching current	ΙL	T <sub>J</sub> = 25 °C, and	ode supply = 6 \	/, resistive load	400	

#### Notes

<sup>(1)</sup>  $I^2t$  for time  $t_x = I^2\sqrt{t} \ x \ \sqrt{t_x}$ 

<sup>&</sup>lt;sup>(2)</sup> Average power =  $V_{T(TO)} \times I_{T(AV)} + r_t \times (I_{T(RMS)})^2$ 

<sup>(3) 16.7 %</sup> x  $\pi$  x  $I_{AV}$  < I <  $\pi$  x  $I_{AV}$ 

 $<sup>^{(4)}~</sup>I>\pi~x~I_{AV}$ 



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TRIGGERING						
PARAMETER	SYMBOL	TEST CO	NDITIONS	VALUES	UNITS	
Maximum peak gate power	$P_{GM}$			12	W	
Maximum average gate power	P <sub>G(AV)</sub>			3.0	VV	
Maximum peak gate current	I <sub>GM</sub>			3.0	Α	
Maximum peak negative gate voltage	- V <sub>GM</sub>			10		
	V <sub>GT</sub>	T <sub>J</sub> = - 40 °C	Anode supply = 6 V resistive load	4.0	V	
Maximum gate voltage required to trigger		T <sub>J</sub> = 25 °C		2.5		
		T <sub>J</sub> = 125 °C		1.7		
		T <sub>J</sub> = - 40 °C	Anode supply = 6 V resistive load	270		
Maximum gate current required to trigger	I <sub>GT</sub>	T <sub>J</sub> = 25 °C		150	mA	
		T <sub>J</sub> = 125 °C		80		
Maximum gate voltage that will not trigger	$V_{GD}$	T <sub>J</sub> = 125 °C, rated V <sub>DRM</sub> applied		0.25	V	
Maximum gate current that will not trigger	I <sub>GD</sub>	$T_J = 125$ °C, rated $V_{DRN}$	<sub>A</sub> applied	6	mA	

BLOCKING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum peak reverse and off-state leakage current at V <sub>RRM</sub> , V <sub>DRM</sub>	I <sub>RRM,</sub> I <sub>DRM</sub>	T <sub>J</sub> = 125 °C, gate open circuit	15	mA				
Maximum RMS insulation voltage	V <sub>INS</sub>	50 Hz	3000 (1 min) 3600 (1 s)	V				
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J$ = 125 °C, linear to 0.67 $V_{DRM}$	1000	V/µs				

THERMAL AND MECHA	THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Junction operating and storage temperature range		T <sub>J</sub> , T <sub>Stg</sub>		-40 to +125	ů		
Maximum internal thermal resistance, junction to case per leg		R <sub>thJC</sub>	DC operation	0.22	°C/W		
Typical thermal resistance, case to heatsink per module		R <sub>thCS</sub>	Mounting surface flat, smooth and greased	0.1	G/ <b>VV</b>		
Mounting torque + 10.0/	to heatsink		A mounting compound is recommended and the torque should be rechecked after a period of	4	Nm		
Mounting torque ± 10 % busbar			3 hours to allow for the spread of the compound.	3	INIII		
Approximate weight				75	g		
Approximate weight				2.7	OZ.		
Case style			JEDEC®	AAP Gen 7	(TO-240AA)		

△R CONDUCTION PER JUNCTION											
DEVICES	8	SINE HALF WAVE CONDUCTION					CTANGUL	AR WAVE C	CONDUCTION	NC	UNITS
DEVICES	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	UNITS
VSK.91	0.04	0.048	0.063	0.085	0.125	0.033	0.052	0.067	0.088	0.127	°C/W

#### Note

• Table shows the increment of thermal resistance R<sub>thJC</sub> when devices operate at different conduction angles than DC

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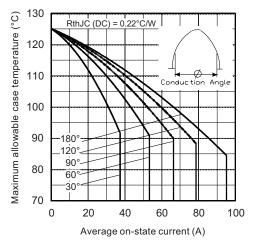


Fig. 1 - Current Ratings Characteristics

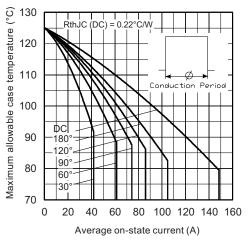


Fig. 2 - Current Ratings Characteristics

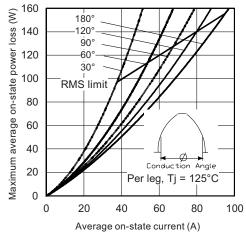


Fig. 3 - On-State Power Loss Characteristics

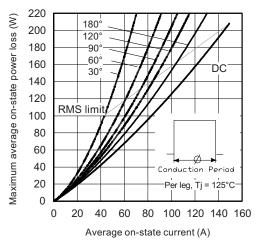


Fig. 4 - On-State Power Loss Characteristics

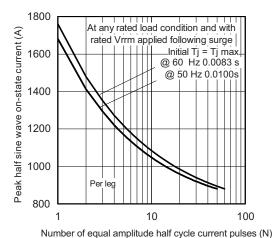


Fig. 5 - Maximum Non-Repetitive Surge Current

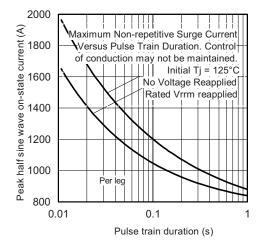


Fig. 6 - Maximum Non-Repetitive Surge Current

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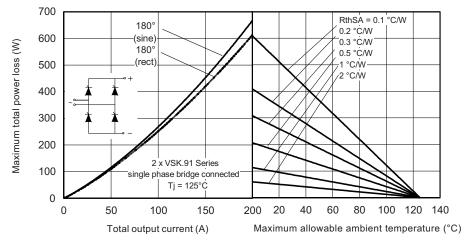


Fig. 7 - On-State Power Loss Characteristics

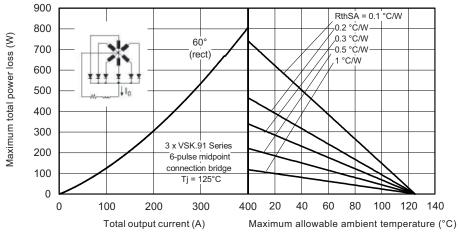


Fig. 8 - On-State Power Loss Characteristics

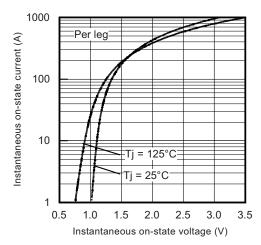


Fig. 9 - On-State Voltage Characteristics

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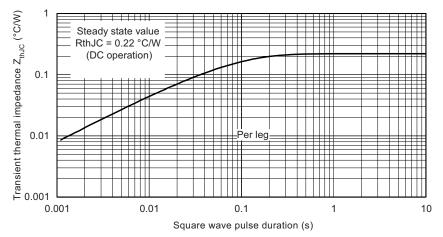


Fig. 10 - Thermal Impedance Z<sub>thJC</sub> Characteristics

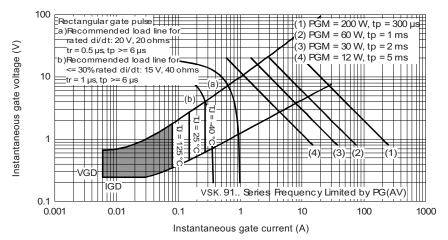
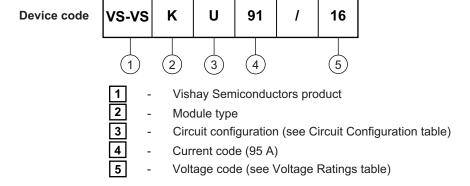


Fig. 11 - Gate Characteristics

#### **ORDERING INFORMATION TABLE**



#### Note

• To order the optional hardware go to <a href="https://www.vishay.com/doc?95172">www.vishay.com/doc?95172</a>

# VS-VSKU91.., VS-VSKV91.. Series

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CIRCUIT CONFIGURATION		
CIRCUIT DESCRIPTION	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING
Two SCRs common cathodes	U	VSKU  (1)  1  2  (2)  (3)  (3)  (3)  (4)  (5)  (7)  (6)
Two SCRs common anodes	V	VSKV (1)  1  2  45 76  (3)  (3)  (3)  (3)  (4) (5) (7) (6)

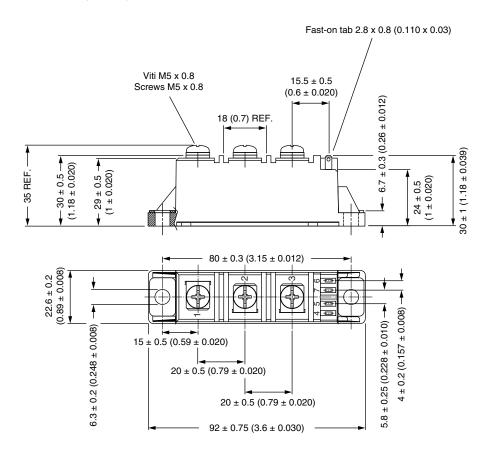
LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95368			



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## **ADD-A-PAK Generation VII - Thyristor**

### **DIMENSIONS** in millimeters (inches)





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